MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK20V60W

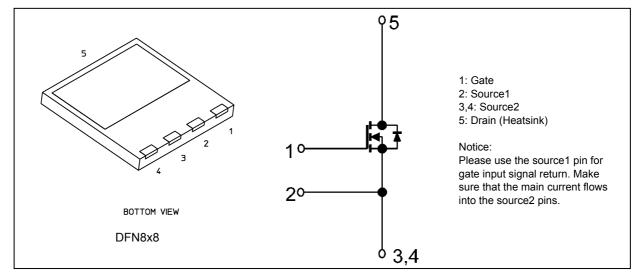
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.136 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{\rm th}$ = 2.7 to 3.7 V (V_{\rm DS} = 10 V, $I_{\rm D}$ = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	20	A
Drain current (pulsed)	(Note 1)	I _{DP}	80	
Power dissipation (T _c =	25°C)	PD	156	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	200	mJ
Avalanche current		I _{AR}	5	A
Reverse drain current (DC)	(Note 1)	I _{DR}	20	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	80	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2013-03

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		0.8	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C. Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 14 mH, R_G = 25 Ω , I_{AR} = 5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	—	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	—	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.7	—	3.7	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 10 A		0.136	0.17	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	1680	_	pF
Reverse transfer capacitance	C _{rss}]		7	_	
Output capacitance	C _{oss}	1		40	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V		70	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz		1.5	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		25		ns
Switching time (turn-on time)	t _{on}]		50	_	
Switching time (fall time)	t _f]		6	_	
Switching time (turn-off time)	t _{off}	1	_	100	_	
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 5 A	50	_	_	V/ns

 $V_{GS}^{10 V} \downarrow I_D = 10 \text{ A } V_{OUT}^{OUT}$

Duty \leq 1 %, t_w = 10 μ s

Fig. 6.2.1 Switching Time Test Circuit

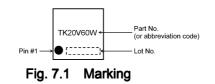
6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 20 \text{A}$	_	48	_	nC
Gate-source charge 1	Q _{gs1}		_	11	_	
Gate-drain charge	Q _{gd}		_	22	_	

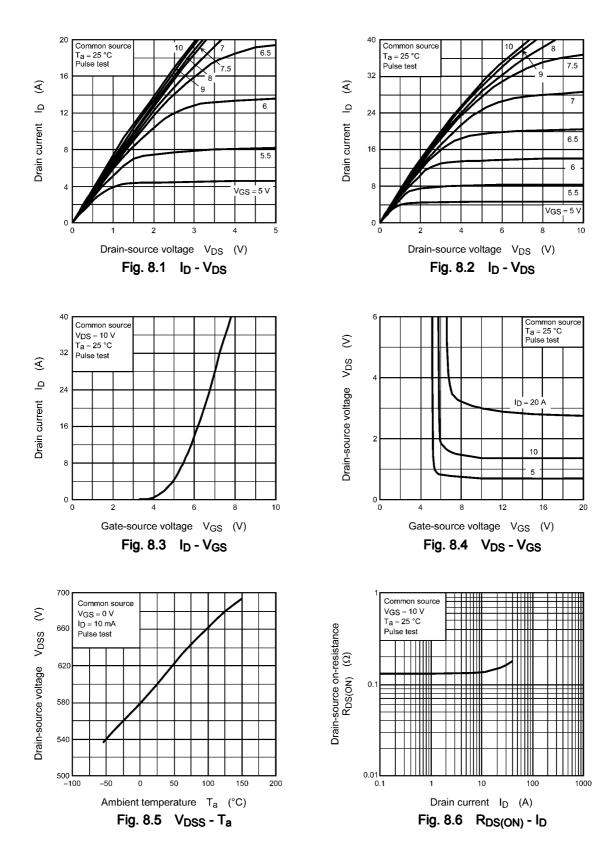
6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

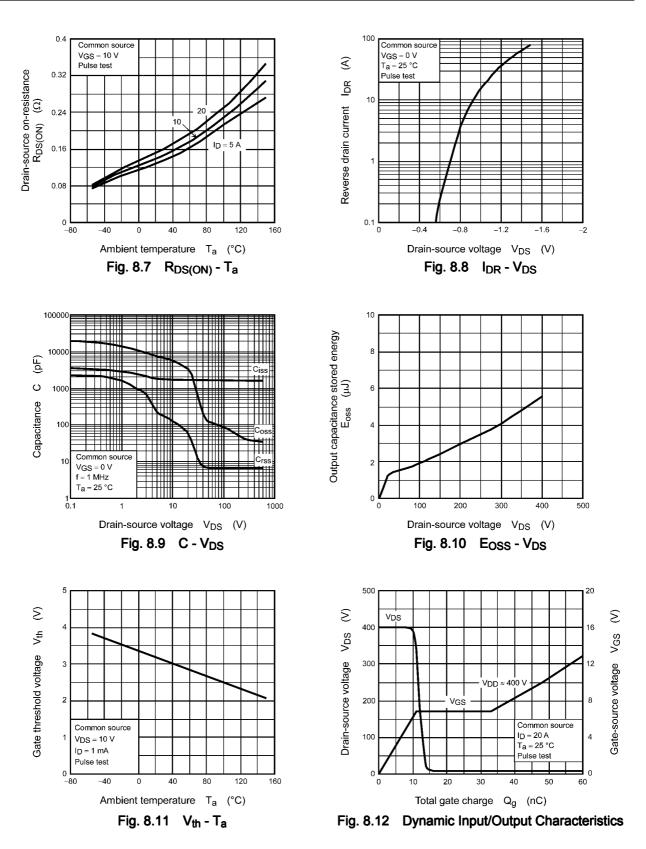
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V	_	330	—	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 50 A/μs	_	2.9	_	μC
Peak reverse recovery current	I _{rr}		_	16	_	А
Diode dv/dt ruggedness	dv/dt	I _{DR} = 10 A, V _{GS} = 0 V, V _{DD} = 400 V	15			V/ns

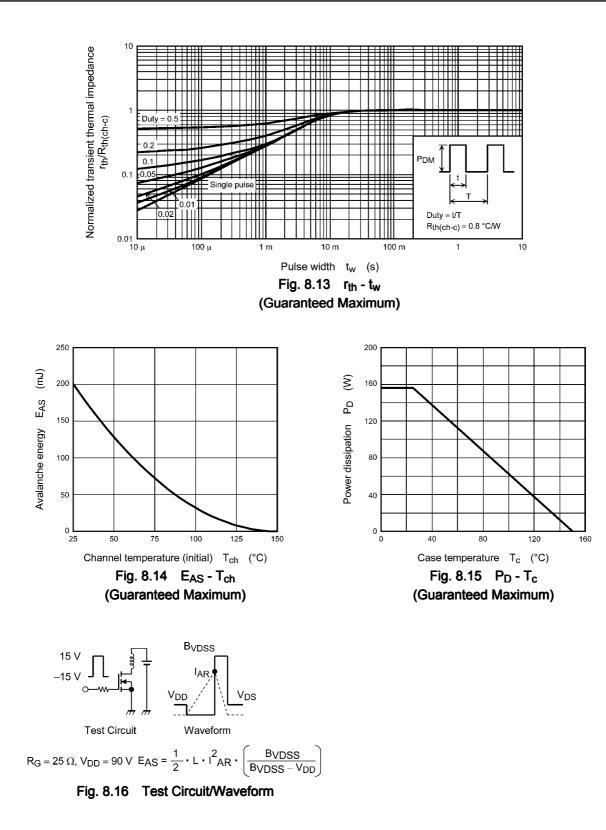
7. Marking

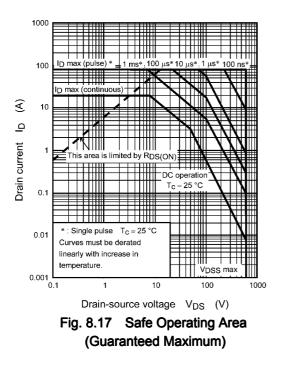


8. Characteristics Curves (Note)









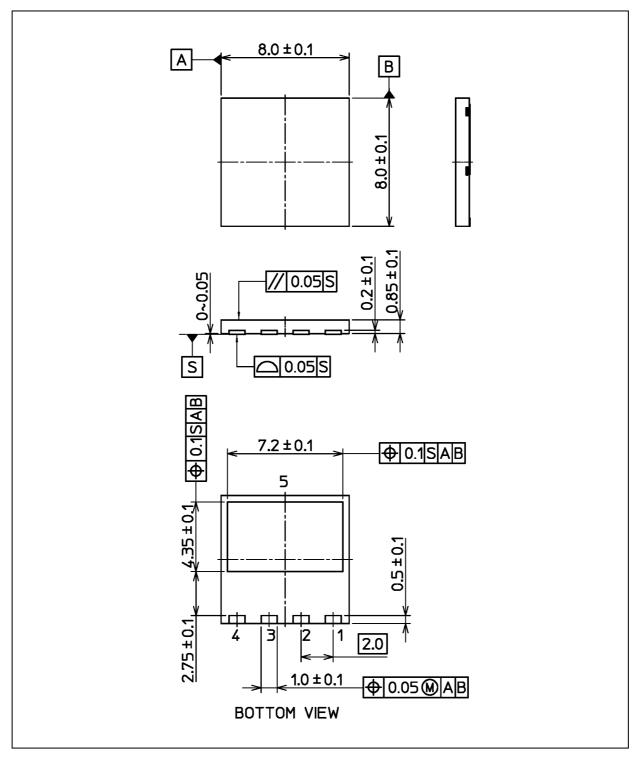
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

TK20V60W

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	

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